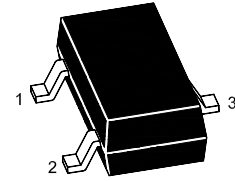




Features

- For switching and AF amplifier applications.
- As complementary type of the NPN transistor FMMT493 is recommended.

SOT-23
(TO-236)



1.Base 2.Emitter 3.Collector

Marking : 593

Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	120	V
Collector Emitter Voltage	$-V_{CEO}$	100	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	1	A
Power Dissipation	P_D	250	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to 150	°C



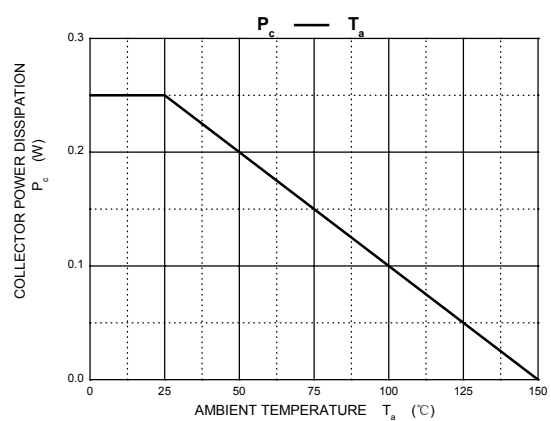
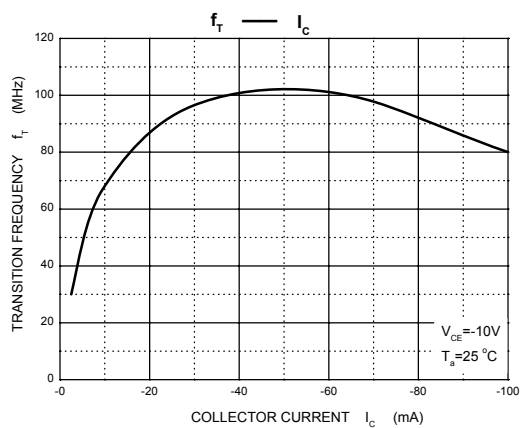
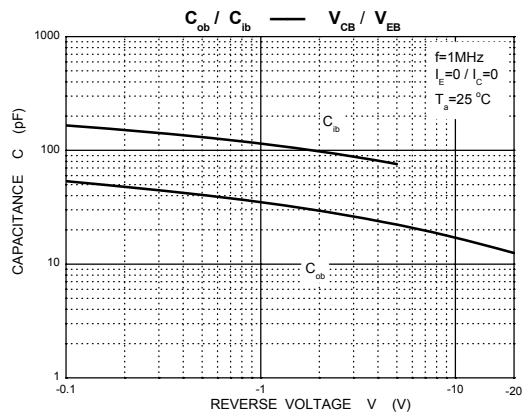
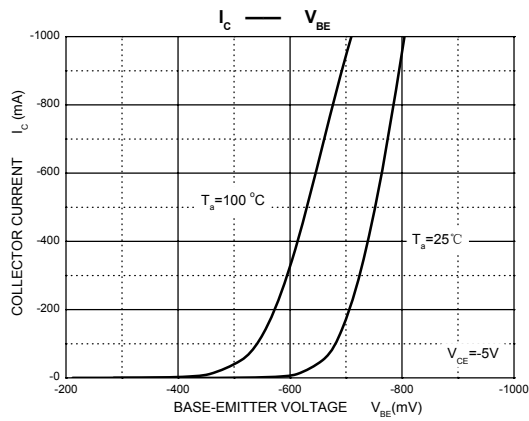
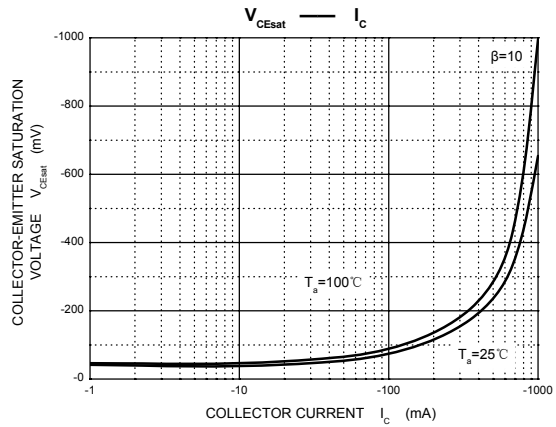
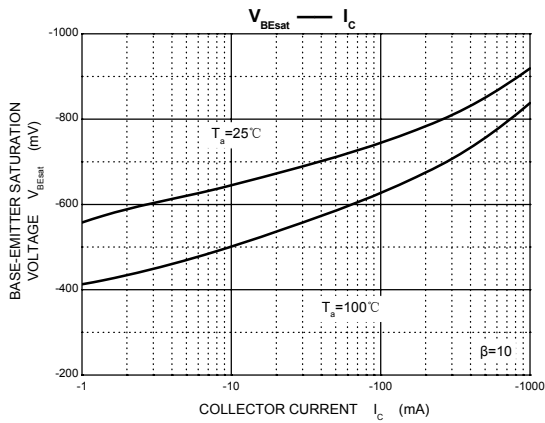
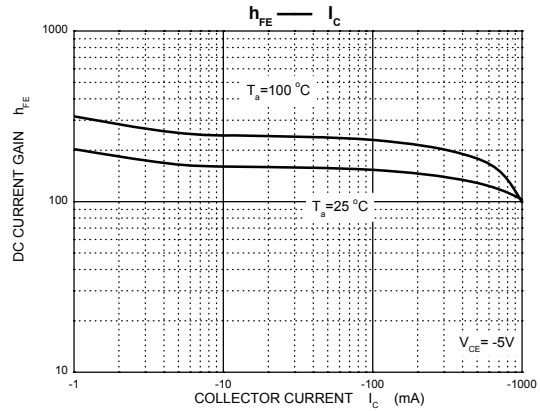
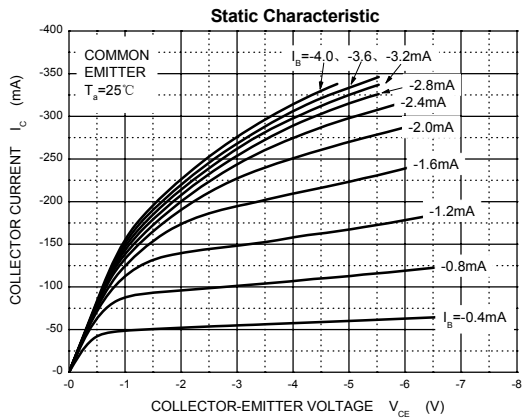
Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain ^{Note1} at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 250\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 0.5\text{ A}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ A}$	H_{FE}	100 100 100 50	-	- - 300 -	-
Collector Base Cutoff Current at $-V_{CB} = 100\text{ V}$	$-I_{CBO}$	-	-	0.1	μA
Collector Base Cutoff Current at $-V_{CE} = 100\text{ V}$	$-I_{CES}$	-	-	0.1	μA
Emitter Base Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	120	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	100	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 250\text{ mA}$, $-I_B = 25\text{ mA}$ at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.2 0.3	V
Base Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{BE(sat)}$	-	-	1.1	V
Base Emitter Voltage at $-V_{CE} = 5\text{ V}$, $-I_B = 1\text{ mA}$	$-V_{BE(on)}$	-	-	1.0	V
Transition Frequency at $-V_{CE} = 10\text{ V}$, $-I_C = 50\text{ mA}$, $f = 100\text{ MHz}$	F_T	150	-	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	5	pF

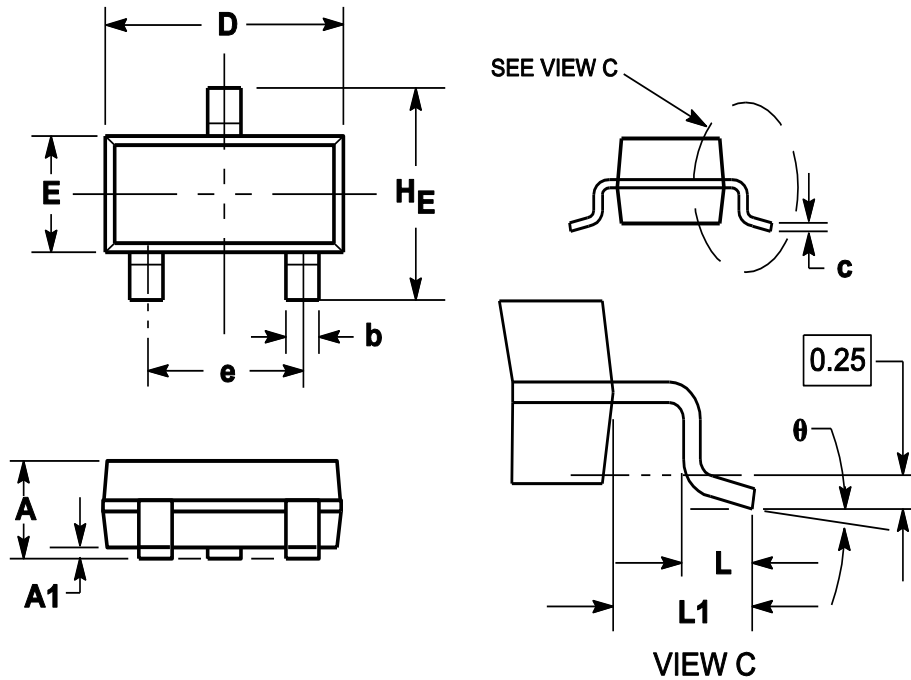


Typical Characteristics Curves





Package Outline(SOT-23)



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.050	0.100
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
HE	2.250	2.400	2.550
e	1.800	1.900	2.000
L1	0.550REF		
L	0.300		0.500
θ	0°		8°

Ordering Information

Device	Package	Reel Dimension (inch)	Shipping
FMMT593	SOT-23	7	3,000

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